Technical Data Sheet

ACS Material Graphene Oxide

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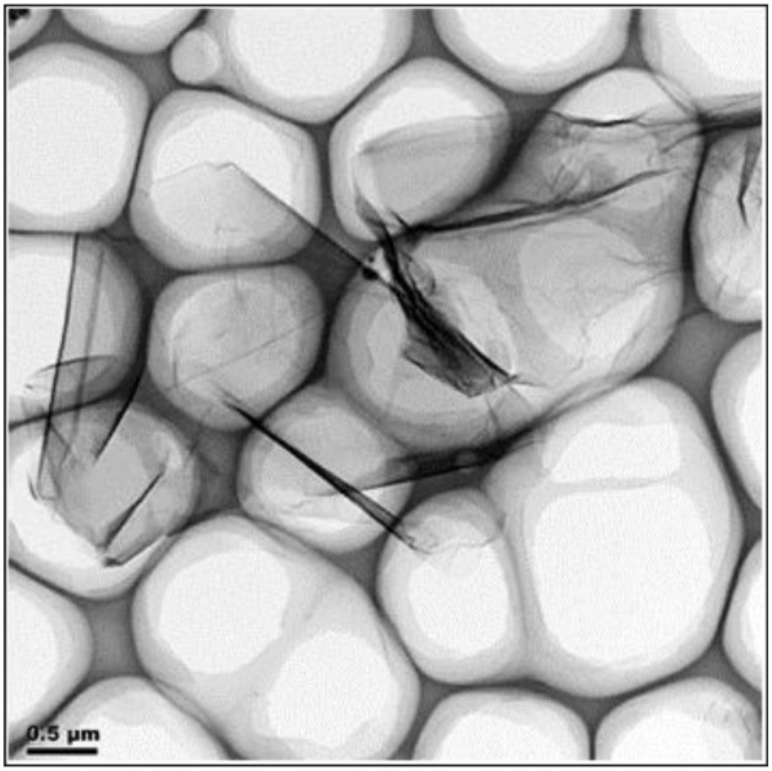
Revision: 061517

1. Preparation Method

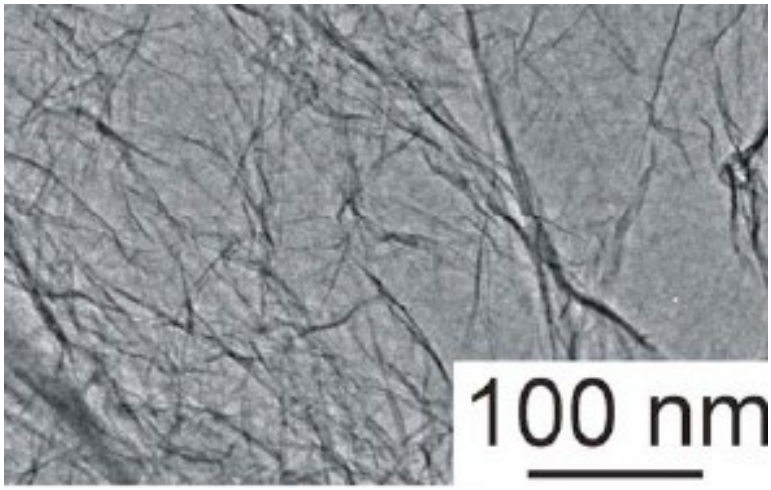
Modified Hummer's Method

2. Characterizations

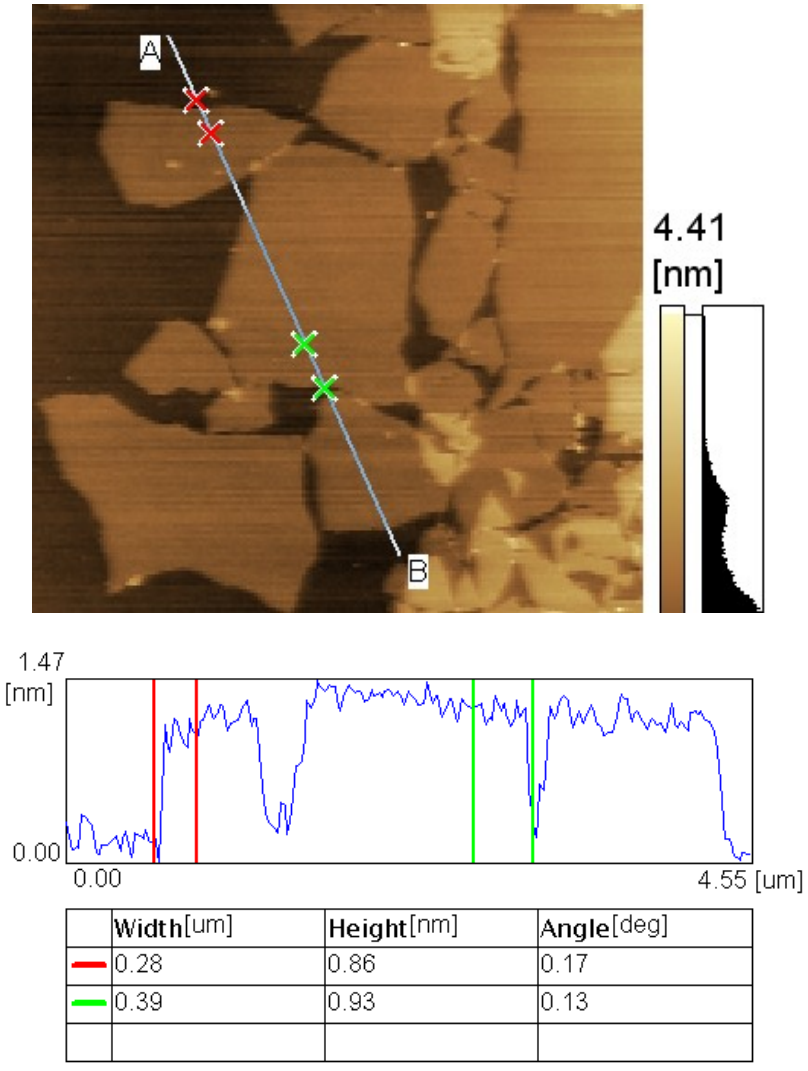
Purity:	~ 99%
Diameter:	1-5 μm
Thickness:	0.8-1.2 nm
Singer layer Ratio:	>80%



Typical TEM Image (1) of ACS Material Single Layer Graphene Oxide (H Method)



Typical TEM Image (2) of ACS Material Single Layer Graphene Oxide (H Method)



	Width[um]	Height[nm]	Angle[deg]
	0.28	0.86	0.17
	0.39	0.93	0.13

AFM Analysis of ACS Material Single Layer Graphene Oxide (H Method)

➢ The TEM and AFM analysis were completed through dispersing ACS-Material Graphene Oxide into water or ethanol with the help of ultrasound.

Elemental compositions of graphene oxide

Sample	N (wt %)	C (wt %)	O (wt %)	C/O at. ratio
Graphene Oxide	0	51.26	40.78	1.67

3. Application Fields

1) Catalyst
2) Supercapacitors
3) Solar energy
4) Graphene semiconductor chips
5) Conductive graphene film
6) Graphene computer memory
7) Biomaterials
8) Transparent conductive coatings